



US008679876B2

(12) **United States Patent**  
**Chakraborty et al.**

(10) **Patent No.:** **US 8,679,876 B2**  
(45) **Date of Patent:** **Mar. 25, 2014**

(54) **LASER DIODE AND METHOD FOR  
FABRICATING SAME**

5,477,436 A 12/1995 Bertling et al.  
5,592,501 A 1/1997 Edmond et al. .... 372/45  
5,612,567 A 3/1997 Baliga

(75) Inventors: **Arpan Chakraborty**, Goleta, CA (US);  
**Monica Hansen**, Santa Barbara, CA  
(US); **Steven Denbaars**, Goleta, CA  
(US); **Shuji Nakamura**, Santa Barbara,  
CA (US); **George Brandes**, Raleigh, NC  
(US)

(Continued)

FOREIGN PATENT DOCUMENTS

EP 1189289 A1 3/1920  
EP 1313187 A1 5/1921

(Continued)

(73) Assignee: **Cree, Inc.**, Goleta, CA (US)

OTHER PUBLICATIONS

(\*) Notice: Subject to any disclaimer, the term of this  
patent is extended or adjusted under 35  
U.S.C. 154(b) by 698 days.

M. Hansen et al., "Effect of AlGaIn/GaN Strained Layer Superlattice  
Period on InGaIn MQW Laser Diodes," phys. Stat. sol. (a) 176,  
(1999) pp. 59-62.\*

(21) Appl. No.: **12/826,305**

(Continued)

(22) Filed: **Jun. 29, 2010**

*Primary Examiner* — Xinning Niu

(65) **Prior Publication Data**

US 2010/0273281 A1 Oct. 28, 2010

(74) *Attorney, Agent, or Firm* — Koppel, Patrick, Heybl &  
Philpott

**Related U.S. Application Data**

(62) Division of application No. 11/600,604, filed on Nov.  
15, 2006, now Pat. No. 7,769,066.

(51) **Int. Cl.**  
**H01L 21/00** (2006.01)

(52) **U.S. Cl.**  
USPC ..... **438/31**; 372/45.012; 372/43.01;  
372/45.011

(58) **Field of Classification Search**  
USPC ..... 372/45.012; 438/31  
See application file for complete search history.

(56) **References Cited**

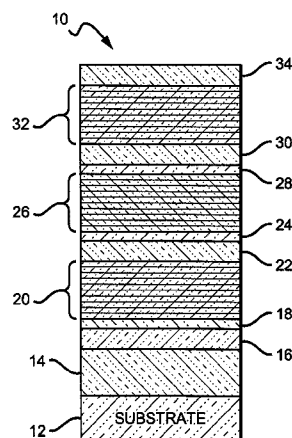
U.S. PATENT DOCUMENTS

3,896,479 A 7/1975 Di Lorenzo  
4,152,044 A 5/1979 Liu  
4,675,575 A 6/1987 Smith et al.

(57) **ABSTRACT**

A laser diode and method for fabricating same, wherein the  
laser diode generally comprises an InGaIn compliance layer  
on a GaIn n-type contact layer and an AlGaIn/GaIn n-type  
strained super lattice (SLS) on the compliance layer. An  
n-type GaIn separate confinement heterostructure (SCH) is on  
said n-type SLS and an InGaIn multiple quantum well  
(MQW) active region is on the n-type SCH. A GaIn p-type  
SCH on the MQW active region, an AlGaIn/GaIn p-type SLS  
is on the p-type SCH, and a p-type GaIn contact layer is on the  
p-type SLS. The compliance layer has an In percentage that  
reduces strain between the n-type contact layer and the n-type  
SLS compared to a laser diode without the compliance layer.  
Accordingly, the n-type SLS can be grown with an increased  
Al percentage to increase the index of refraction. This along  
with other features allows for reduced threshold current and  
voltage operation.

**24 Claims, 4 Drawing Sheets**



(56)

## References Cited

## U.S. PATENT DOCUMENTS

5,705,321 A 1/1998 Brueck et al. .... 430/316  
 5,812,576 A 9/1998 Bour ..... 372/45.01  
 5,838,706 A 11/1998 Edmond et al. .... 372/45  
 6,046,464 A 4/2000 Schetzina  
 6,144,683 A 11/2000 Floyd ..... 372/50.12  
 6,172,382 B1 \* 1/2001 Nagahama et al. .... 257/94  
 6,330,111 B1 12/2001 Myers  
 6,331,915 B1 12/2001 Myers  
 6,372,536 B1 4/2002 Fischer et al. .... 438/46  
 6,504,179 B1 1/2003 Ellens et al. .... 257/88  
 6,521,915 B2 2/2003 Odaki et al. .... 257/98  
 6,611,003 B1 \* 8/2003 Hatakoshi et al. .... 257/98  
 6,657,393 B2 12/2003 Natsume  
 6,693,357 B1 2/2004 Borst et al. .... 257/773  
 6,746,889 B1 6/2004 Eliashevich et al.  
 6,765,242 B1 7/2004 Chang et al. .... 257/197  
 6,784,463 B2 8/2004 Camras et al.  
 6,932,497 B1 8/2005 Huang  
 7,087,936 B2 8/2006 Negley  
 2002/0015013 A1 2/2002 Ragle  
 2002/0054495 A1 5/2002 Natsume  
 2003/0015708 A1 1/2003 Parikh  
 2003/0085409 A1 5/2003 Shen  
 2004/0057482 A1 \* 3/2004 Wang ..... 372/45  
 2004/0207313 A1 10/2004 Omoto et al.  
 2004/0233957 A1 11/2004 Ito et al.  
 2004/0262576 A1 12/2004 Thompson et al. .... 252/301.16  
 2005/0030995 A1 \* 2/2005 Kawakami et al. .... 372/43  
 2005/0048766 A1 \* 3/2005 Wu et al. .... 438/629  
 2005/0077535 A1 4/2005 Li  
 2005/0117320 A1 6/2005 Leu et al.  
 2005/0152127 A1 7/2005 Kamiya et al.  
 2005/0173692 A1 8/2005 Park  
 2005/0173728 A1 8/2005 Saxler  
 2005/0213625 A1 \* 9/2005 Horie ..... 372/44.01  
 2005/0220046 A1 10/2005 Yu et al.  
 2006/0081862 A1 4/2006 Chua et al.  
 2006/0158899 A1 7/2006 Avabe et al.  
 2006/0267031 A1 11/2006 Tasch et al.  
 2007/0090383 A1 4/2007 Ota  
 2007/0268694 A1 11/2007 Bailey et al. .... 362/231  
 2008/0023689 A1 1/2008 Kim et al. .... 257/13  
 2008/0036364 A1 2/2008 Li et al.  
 2008/0074032 A1 3/2008 Yano et al.  
 2010/0273281 A1 10/2010 Chakraborty et al.  
 2011/0193057 A1 8/2011 Sabathil et al.

## FOREIGN PATENT DOCUMENTS

EP 1063711 A1 12/1927  
 EP 0 272 985 A2 6/1988  
 EP 0881666 A2 12/1998  
 EP 0936382 8/1999  
 EP 1653255 5/2006  
 EP 1681509 7/2006  
 EP 2048718 4/2009  
 FR 2586844 3/1987  
 FR 2759188 8/1998  
 FR 2814220 3/2002  
 JP 11330552 11/1966  
 JP S63-288061 11/1988  
 JP H05-075101 3/1993  
 JP H05-283672 10/1993  
 JP 3191447 5/1994  
 JP 6268257 A 9/1994  
 JP 7162038 A 6/1995  
 JP 7176826 A 7/1995  
 JP 8023124 A 1/1996  
 JP 8070139 A 3/1996  
 JP 8162671 A 6/1996  
 JP 8274414 A 10/1996  
 JP 9330630 A 12/1996  
 JP 9148678 A 6/1997  
 JP 9153642 A 6/1997

JP 9162444 A 6/1997  
 JP 11040850 7/1997  
 JP 9219556 A 8/1997  
 JP 10012969 A 1/1998  
 JP 10041581 A 2/1998  
 JP 10065271 3/1998  
 JP 10145000 A 5/1998  
 JP 10145002 A 5/1998  
 JP 10033557 A 12/1998  
 JP 11074562 A 3/1999  
 JP 11186659 A 7/1999  
 JP 11191638 A 7/1999  
 JP 11224972 A 8/1999  
 JP 11238945 A 8/1999  
 JP 11251684 A 9/1999  
 JP 11298090 A 10/1999  
 JP 2000-049363 2/2000  
 JP 20000685 A 3/2000  
 JP 2000-150920 5/2000  
 JP 2000133883 A 5/2000  
 JP 2000150956 A 5/2000  
 JP 2000244072 A 9/2000  
 JP 2000307149 A 11/2000  
 JP 2001168471 6/2001  
 JP 2001332770 A 11/2001  
 JP 2002512379 4/2002  
 JP 2002543594 12/2002  
 JP 2002543594 A 12/2002  
 JP 2003-59938 2/2003  
 JP 2003-152219 5/2003  
 JP 2003258313 A 9/2003  
 JP 2003318449 A 11/2003  
 JP 2004276383 10/2004  
 JP 2004281605 10/2004  
 JP 2005228833 8/2005  
 JP 2007-036010 2/2007  
 JP 2007-189239 7/2007  
 JP 2007189239 7/2007  
 JP 2009094517 4/2009  
 WO WO 9831055 A1 7/1998  
 WO WO 98/37585 A1 8/1998  
 WO WO9856043 12/1998  
 WO WO 9905728 A1 2/1999  
 WO WO 9946822 A1 9/1999  
 WO WO 0021143 4/2000  
 WO WO 0076004 A1 12/2000  
 WO WO 01-41224 6/2001  
 WO WO 02-01608 1/2002  
 WO WO 0205399 A1 1/2002  
 WO WO 02/11212 A 2/2002  
 WO 03044870 5/2003  
 WO WO03080763 10/2003  
 WO WO2004084316 9/2004  
 WO WO2004084316 A2 9/2004  
 WO WO2004109813 12/2004  
 WO WO2004109813 A2 12/2004  
 WO WO2005104247 3/2005  
 WO WO 2005/098976 A 10/2005  
 WO WO2005098976 A2 10/2005  
 WO WO2005119799 12/2005  
 WO 2007005844 A2 1/2007  
 WO WO2007075815 7/2007  
 WO WO 2008/020913 2/2008  
 WO WO2008020913 2/2008

## OTHER PUBLICATIONS

"The American Heritage Dictionary", Library of Congress, New College Ed., 1976, pp. 867.

"Properties of Delta Doped Al<sub>0.25</sub>Ga<sub>0.75</sub>N and GaN Epitaxial Layers", Jeffrey S. Flynn, et al, Materials Research Society, 1 page.

"III-nitride ultraviolet light-emitting diodes with delta doping", K.H. Kim. et al. Applied Physics Letters, vol. 83, No. 3. Jul. 21, 2003, pp. 566-568.

Reduction of threading edge dislocation density in n-type GaN by Si delta-doping, Y.B. Pan. et al, Journal of Crystal Growth 286 (2006) 255-258.

(56)

**References Cited**

## OTHER PUBLICATIONS

Epitaxial Growth and Characterisation of Silicon Delta-Doped GaAs, AlAs and AlGa<sub>x</sub>As, B. Sciana, et al, Crystal Res. Technol. 36 2001 8-10, pp. 1145-1154.

"Effects of periodic delta-doping on the properties of GaN:Si films grown on Si (111) substrates" L.S. Wang, et al, Applied Physics Letters. vol. 85, No. 34, Dec. 13, 2004. pp. 5881-5884.

"The effect of periodic silane burst on the properties of GaN on Si (111) substrates", Zang Keyan, et al, Singapore-MIT Alliance. E4-04-10 & Dept. of Materials Science and Engineering 4 pages.

European Search Report. EP 03 07 8515, dated: Feb. 2, 2004.

Partial European Search Report, EP 09 15 7557. dated: May 28, 2009. Non-final Rejection. Korean Appl. No. 10-2003-7012710, dated: Aug. 8, 2008.

Non-final Rejection. Korean Appl. No. 10-2008-7026427. dated: Jan. 23, 2009.

Office Action from U.S. Appl. No. 11/900,952, dated: Nov. 17, 2011. Response to Office Action from U.S. Appl. No. 11/900,952, filed Mar. 19, 2012.

Office Action from U.S. Appl. No. 11/974,431, dated: Nov. 29, 2011. Summary of Decision of Rejection from Japanese Patent Application No. 2008-262602, dated May 8, 2012.

Notice of Reasons for Rejection for Japanese Patent Application No. JP 2007-143451 dated May 10, 2011.

Extended Search Report for European Patent Application No. 11154411.0 dated May 30, 2011.

Singh Madhusudan, et al., "Examination of Tunnel Junctions in the AlGa<sub>N</sub>/Ga<sub>N</sub> System: Consequences of Polarization Charge", Applied Physics Letters, AIP, American Institute of Physics, Melville, NY, vol. 77, No. 12, Sep. 18, 2000, pp. 1867-1969.

Panda A.K. et al., "DC and High-Frequency Characteristics of GaN Based Impatts", IEEE Transactions on Electron Devices, IEEE Service Center, Piscataway, NJ, US vol. 48, No. 4, Apr. 1, 2001, pp. 820-823.

Decision of Rejection and Decision of Dismissal of Amendment from Japanese Patent Application No. 2007-143451, dated Nov. 13, 2012.

First Notice of Office Action, dated: May 8, 2009, for Chinese Application No. 200710142217.6, pp. 1-3.

Office Action from U.S. Appl. No. 11/600,617, dated Dec. 22, 2009.

Office Action for U.S. Appl. No. 11/600,604, dated: May 14, 2008.

Response to Office Action filed on Sep. 15, 2008 for U.S. Appl. No. 11/600,604.

Response to Office Action filed on Nov. 24, 2008 for U.S. Appl. No. 11/600,604.

Office Action for U.S. Appl. No. 11/600,604, dated: Feb. 11, 2009.

Office Action for U.S. Appl. No. 11/600,604, dated: May 12, 2009.

Response to Office Action filed on Apr. 13, 2009 for U.S. Appl. No. 11/600,604.

Response to Office Action filed on Jun. 11, 2009 for U.S. Appl. No. 11/600,604.

Response to Office Action filed on Jun. 30, 2009 for U.S. Appl. No. 11/600,604.

Office Action for U.S. Appl. No. 11/600,604, dated: Sep. 16, 2009.

Response to Office Action filed on Dec. 11, 2009 for U.S. Appl. No. 11/600,604.

Notice of Allowance for U.S. Appl. No. 11/600,604, dated: Mar. 23, 2010.

International Search Report for PCT/US2008/004453, Date: Sep. 9, 2008.

Written Opinion for PCT/US2008/004453, Date: Sep. 9, 2008.

Kim J K et al. "Strongly Enhanced Phosphor Efficiency in GaInN White Light-Emitting Diodes Using Remote Phosphor Configuration and Diffuse Reflector Cup", Japanese Journal of Applied Physics, Japan Society of Applied Physics, Tokyo, JP, vol. 44, No. 20-23, Jan. 1, 2005, XP-001236966.

The Second Office Action from People's Republic of China, re: China Application No. 200480027969.2, Date: Jul. 4, 2008.

Notice of First Office Action from related China Patent Application No. 200710142217.6, dated: Jun. 22, 2009.

Official Communication from the EPO regarding European Application 08253301.9, dated: Nov. 17, 2009.

Second Office Action from Chinese Application No. 200710142217.6, dated: Nov. 6, 2009.

Notice Requesting Submission of Opinion re related Korean application No. 10-2004-7001033, dated: Mar. 9, 2009.

Zhang et al. "Comparison of GaN P-I-N and Schottky Rectifier Performance", IEEE Transactions on Electron Devices, vol. 48, No. 3, Mar. 2001, pp. 407-411.

Sakai et al., "Experimental Investigation of Dependence of Electrical Characteristics on Device Parameters in Trench MOS Barrier Schottky Diodes", 1998, International Symposium on Power Semiconductor Devices & ICs, Kyoto, pp. 293-296.

European Search Report re related European Application No. 08253301.9-2222. Feb. 24, 2009.

European Search Report re related EP Appl. 08160129.6-2222, Dated: Dec. 15, 2008.

Copending U.S. Appl. No. 11/443,741, filed Jun. 14, 2007.

Copending U.S. Appl. No. 11/685,761, filed Mar. 13, 2007.

Copending U.S. Appl. No. 11/939,059, filed Nov. 13, 2007.

Asbeck et al. "Enhancement of Base Conductivity Via the Piezoelectric Effect in AlGa<sub>N</sub>/Ga<sub>N</sub> HBTs", Solid State Electronics, Elsevier Science Pub. Barking GB, vol. 44, No. 2, Feb. 1, 2000 pp. 211-219, XP004186190.

Johnson et al. "New UV Light Emitter Based on AlGa<sub>N</sub> Heterostructures with Graded Electron and Hole Injectors", Materials Research Society Symposium—Proceedings 2002 Materials Research Society US, vol. 743, 2002, pp. 481-486.

Simon et al. "Polarization-Induced 3-Dimensional Electron Slabs in Graded AlGa<sub>N</sub> Layers", Materials Research Society Symposium Proceedings 2006 Materials Research Society US, vol. 892, Nov. 28, 2005, pp. 417-422.

Official Notice of Final Decision of Rejection Japanese Patent Appl. No. 2003-529535, Dated: Jan. 6, 2009.

European Communication from European Appl. 02 798 906.0-1235, Dated Feb. 6, 2009.

PCT Search Report and Written Opinion PCT/US2007/086237, date: May 8, 2008 in related application.

PCT Search Report and Written Opinion PCT/US2007/12403, Date: Aug. 6, 2008.

PCT Search Report and Written Opinion PCT/US2007/086242, Date: Mar. 4, 2008.

U.S. Appl. No. 11/613,692, filed Dec. 20, 2006.

U.S. Appl. No. 11/614,180, filed Dec. 21, 2006.

U.S. Appl. No. 11/624,811, filed Jan. 19, 2007.

U.S. Appl. No. 11/743,754, filed May 3, 2007.

U.S. Appl. No. 11/751,982, filed May 22, 2007.

U.S. Appl. No. 11/753,103, filed May 24, 2007.

U.S. Appl. No. 11/751,990, filed May 22, 2007.

U.S. Appl. No. 11/755,153, filed May 30, 2007.

U.S. Appl. No. 11/856,421, filed Sep. 17, 2007.

U.S. Appl. No. 11/859,048, filed Sep. 21, 2007.

U.S. Appl. No. 11/939,047, filed Nov. 13, 2007.

U.S. Appl. No. 11/936,163, filed Nov. 7, 2007.

U.S. Appl. No. 11/843,243, filed Aug. 22, 2007.

U.S. Appl. No. 11/939,052, filed Nov. 13, 2007.

U.S. Appl. No. 11/736,799, filed Apr. 18, 2007.

U.S. Appl. No. 11/877,038, filed Oct. 23, 2007.

U.S. Appl. No. 11/870,679, filed Oct. 11, 2007.

U.S. Appl. No. 11/948,041, filed Nov. 30, 2007.

U.S. Appl. No. 11/949,222, filed Dec. 3, 2007.

U.S. Appl. No. 12/174,053, filed Jul. 16, 2008.

U.S. Appl. No. 12/002,429, filed Dec. 4, 2007.

U.S. Appl. No. 12/045,729, filed Mar. 11, 2008.

U.S. Appl. No. 11/818,818, filed Jun. 14, 2007.

Examination of European Patent Application No. 08 253 301.9-2222, dated Apr. 24, 2012.

Decision for Grant for Japanese Patent Application No. 2008-182592, dated Jul. 3, 2012.

Notice of Reasons for Rejection for Japanese Patent Application No. 2007-143451, dated Jul. 31, 2012.

(56)

**References Cited****OTHER PUBLICATIONS**

Notification of National Application Upon the Preliminary Examination of Patent Application from Chinese Patent Application No. 200880100370.5 dated Jun. 1, 2010.

Notification on Publication and Entry into Procedure of Substantive Examination of Invention Patent Application from Chinese Patent Application No. 200880100370.5 dated Aug. 18, 2010.

Office Action from U.S. Appl. No. 11/900,952, Dated: May 26, 2011.

Office Action from U.S. Appl. No. 13/045,246, Dated: Oct. 21, 2011.

Invitation to Submit Applicant's Opinion (Summary) in Japanese Appeal Filing No. 2009-007421, Japanese Patent Application No. 2003-529535 mailed Dec. 7, 2010.

Examiner's Report to the Board (Summary) in Japanese Appeal Filing No. 2009-007421, Japanese Patent Application No. 2003-529535 mailed Dec. 7, 2010.

Summary of Notice of Reasons for Rejection for Japanese Patent Application No. 2008-264568 mailed Nov. 15, 2011.

Summary of Notice of Reasons for Rejection for Japanese Patent Application No. 2008-182592 mailed Nov. 22, 2011.

M.A.L. Johnson, et al., New UV Light Emitter Based on AlGaIn Heterostructures with Graded Electron and Hole Injectors, *Mat. Res. Soc. Symp. Proc.* vol. 743, 2003, pp. 481-486.

Simon, John, et al., Polarization-Induced 3-Dimension Electron Slabs in Graded AlGaIn Layers, *Material Res. Soc. Symp.* vol. 892, 2006, pp. 417-422.

Summary of Notice of Reasons for Rejection for Japanese Patent Application No. JP 2007-292302 mailed Jan. 24, 2012.

Examination Report for European Patent Application No. 07254498.4 dated Jan. 26, 2012.

Appeal Board's Questioning from Japanese Patent Application No. 2008-262602, dated Dec. 14, 2012.

Office Action from U.S. Appl. No. 12/905,374, dated: Mar. 27, 2012.

Office Action from U.S. Appl. No. 13/045,246, dated: Apr. 5, 2012.

Official Action from European Patent Appl. No. 11154411.0. dated Feb. 27, 2013.

Decision of Patent Grant from Japanese Patent Application No. 2007-143451, dated Apr. 16, 2013.

Summary of Notice of Reasons for Rejection for Japanese Patent Application No. 2008-262602 mailed Jul. 12, 2011.

Office Action for Canadian Patent Application No. 2,454,310 dated Aug. 30, 2011.

Summary of Notice of Reasons for Rejection for Japanese Patent Application No. 2007-292302 dated Oct. 4, 2011.

Examination Report from Canadian Patent Appl. No. 2,454,310, dated Sep. 5, 2013.

Hanson, et al., "Effect of AlGaIn/GaN Strained Layer Superlattice Period on InGaIn MQW Laser Diodes", *phys. Stat. sol. (a)* 176, 59 (1999), Materials and Electrical and Computer Engineering Departments University of California, Santa Barbara, CA 93106-5050.

Examination Report from European Patent Appl. No. 07 254 498.1, dated Aug. 9, 2013.

Decision of Appeal from Japanese Patent Appl. No. 2008-262602, dated Jul. 5, 2013.

Office Action from U.S. Appl. No. 11/974,431, dated May 22, 2013.

Response to OA from U.S. Appl. No. 11/974,431, filed Jul. 23, 2013.

Office Action from U.S. Appl. No. 11/900,952, dated May 14, 2012.

Response to OA from U.S. Appl. No. 11/900,952, filed Sep. 14, 2012.

Office Action from U.S. Appl. No. 11/900,952, dated Nov. 17, 2011.

Response to OA from U.S. Appl. No. 11/900,952, filed Mar. 19, 2012.

Office Action from U.S. Appl. No. 11/974,431, dated Nov. 29, 2011.

Response to OA from U.S. Appl. No. 11/974,431, filed May 29, 2012.

Office Action from U.S. Appl. No. 11/974,431, dated Jul. 9, 2012.

Response to OA from U.S. Appl. No. 11/974,431, filed Sep. 26, 2012.

Office Action from U.S. Appl. No. 13/045,246, dated Apr. 5, 2012.

Response to OA from U.S. Appl. No. 13/045,246, filed Jul. 2, 2012.

Office Action from U.S. Appl. No. 11/974,431, dated Feb. 14, 2013.

Response to OA from U.S. Appl. No. 11/974,431, filed May 14, 2013.

Office Action from U.S. Appl. No. 13/045,246, dated Dec. 5, 2012.

Response to OA from U.S. Appl. No. 13/045,246, filed Feb. 21, 2013.

Office Action from U.S. Appl. No. 11/900,952, dated Jan. 15, 2013.

Response to OA from U.S. Appl. No. 11/900,952, filed Apr. 9, 2013.

Office Action from U.S. Appl. No. 13/045,246, dated Aug. 28, 2012.

Response to OA from U.S. Appl. No. 13/045,246, filed Oct. 16, 2012.

Office Action from U.S. Appl. No. 12/905,374, dated Mar. 27, 2012.

Response to OA from U.S. Appl. No. 12/905,374, filed Jun. 27, 2012.

\* cited by examiner

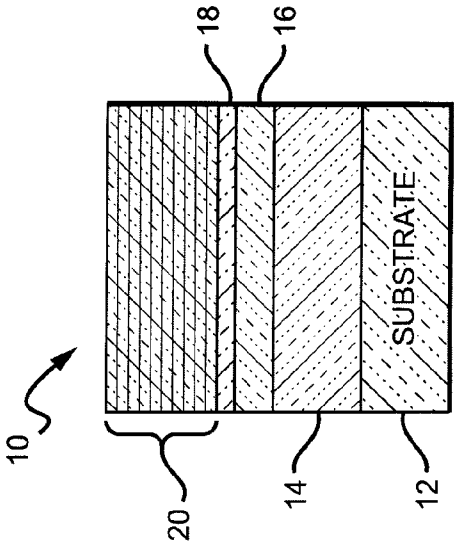


FIG. 3

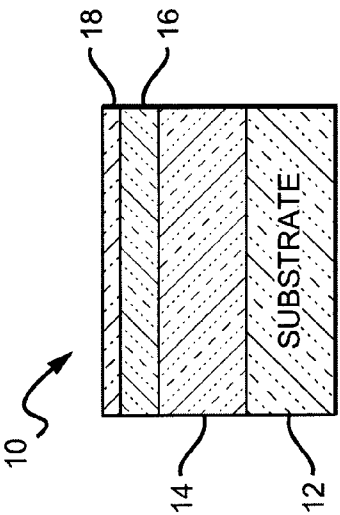


FIG. 2

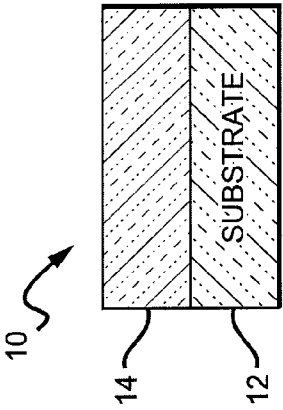


FIG. 1

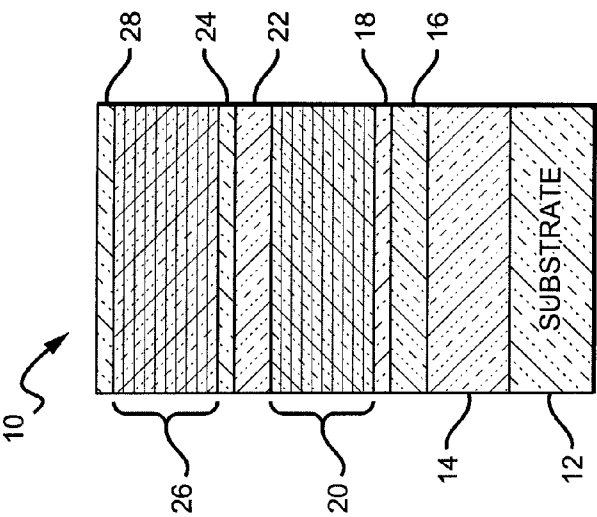


FIG. 6

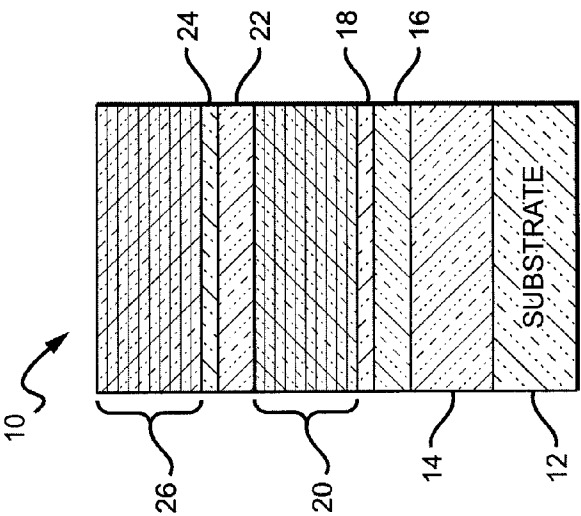


FIG. 5

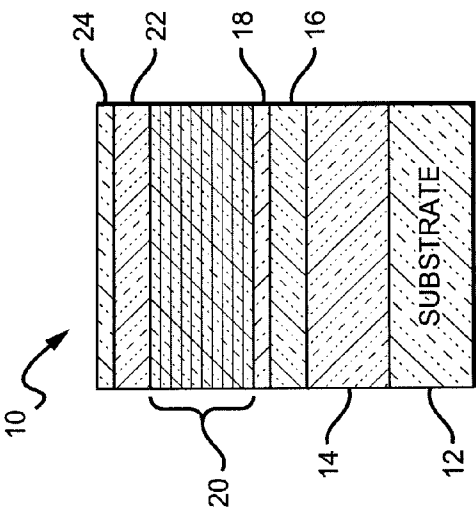


FIG. 4

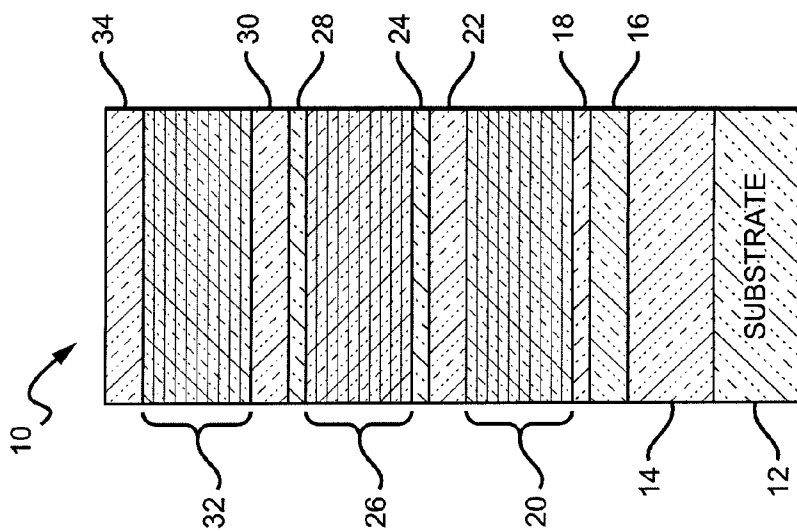


FIG. 9

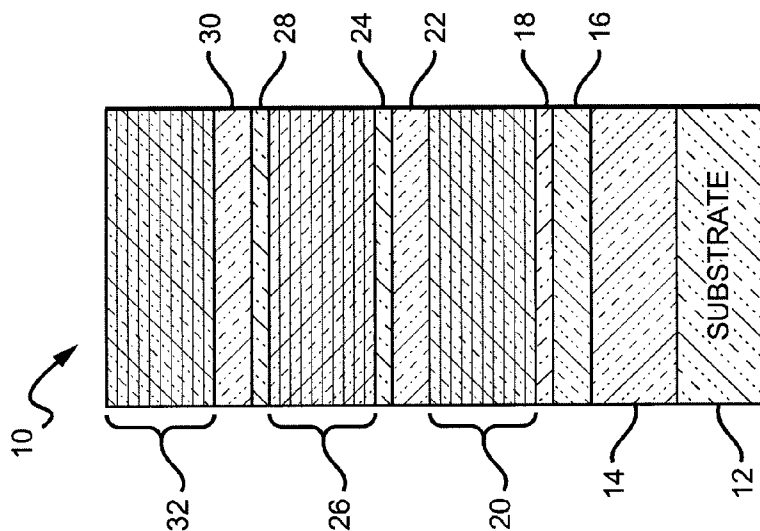


FIG. 8

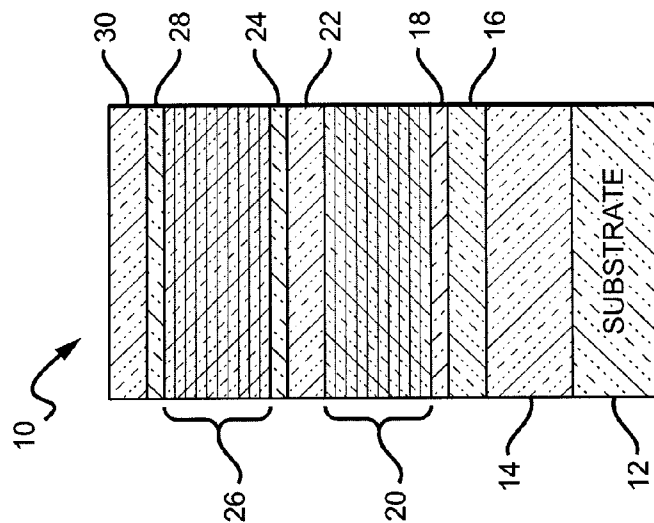
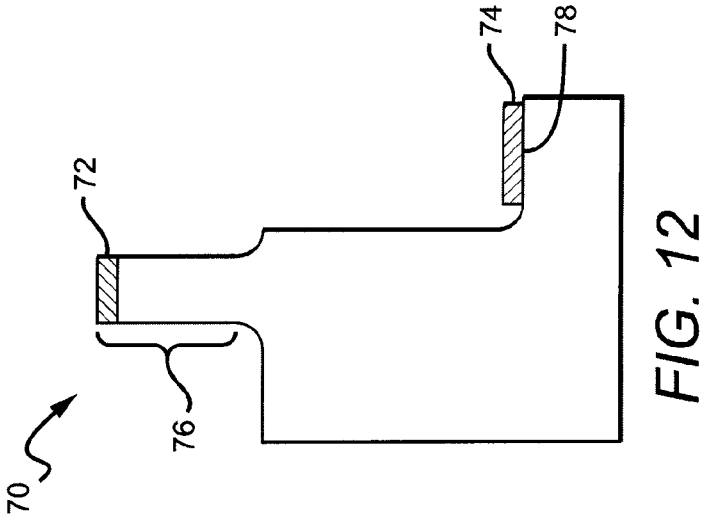
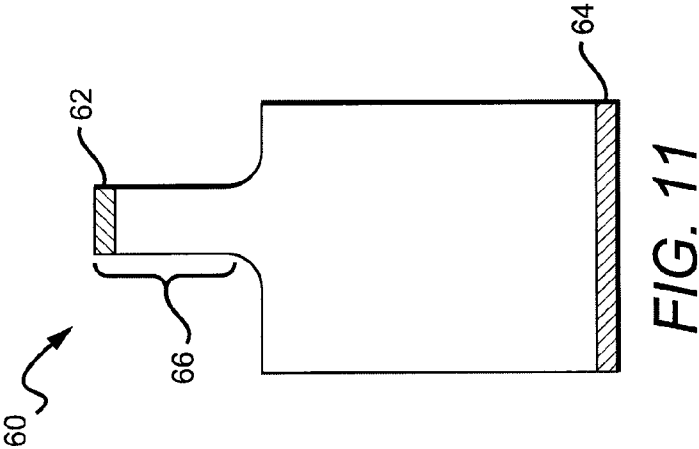
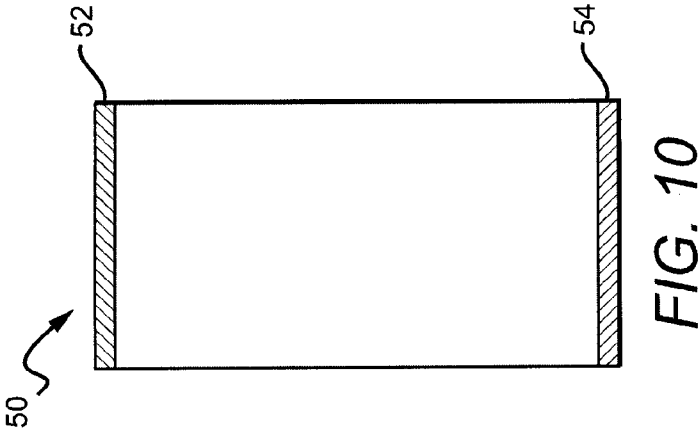


FIG. 7





1

# **LASER DIODE AND METHOD FOR FABRICATING SAME**

This application is a divisional application from, and claims the benefit of, U.S. patent application Ser. No. 11/600,604 filed Nov. 15, 2006 now U.S. Pat. No. 7,769,066 to Chakraborty et al., also entitled "Laser Diode and Method for Fabricating Same."

## **BACKGROUND OF THE INVENTION**

### **1. Field of the Invention**

This invention relates to laser diodes, and more particularly to nitride based semiconductor laser diodes and methods for fabricating same.

### **2. Description of the Related Art**

A laser is a device that produces a beam of coherent light as a result of stimulated emission. Light beams produced by lasers can have high energy because of their single wavelength, frequency, and coherence. A number of materials are capable of producing a lasing effect and include certain high-purity crystals (such as ruby), semiconductors, certain types of glass, certain gasses including carbon dioxide, helium, argon and neon, and certain plasmas.

More recently there has been increased interest in lasers made of semiconductor materials. These devices typically have a smaller size, lower cost, and have other related advantages typically associated with semiconductor devices. Semiconductor lasers are similar to other lasers in that the emitted radiation has spacial and temporal coherence, and like other lasers, semiconductor lasers produce a beam of light that is highly monochromatic (i.e. of narrow bandwidth) and is highly directional. Overall, semiconductor lasers provide very efficient systems that are easily modulated by modulating the current directed across the devices. Additionally, because semiconductor lasers have very short photon lifetimes, they can be used to produce high-frequency modulation.

One type of semiconductor laser diode is referred to as an edge emitting laser where the stimulated emission is from the side surface or edge of the laser diode. These devices typically have epitaxial layers in the form of waveguiding or reflective elements (cladding layers) with a light generating active region between the reflective elements. Additional layers can be included between the reflective elements to form a laser cavity. The edges of the laser diode can be cleaved during manufacturing to form edge reflective surfaces. A total reflectivity (TR) material can cover one edge, and an anti reflectivity (AR) material can cover the opposite edge. Light from the active region is reflected between the edges and within the cavity by the reflective elements, with stimulated emission emitting from the edge with the AR material.

A known characteristic of laser diodes (and light emitting diodes) is that the frequency of radiation that can be produced by the particular laser diode is related to the bandgap of the particular semiconductor material. Smaller bandgaps produce lower energy, shorter wavelength photons, while wider bandgaps produce higher energy, shorter wavelength photons. One semiconductor material commonly used for lasers is indium gallium aluminum phosphide (InGaAlP), which has a bandgap that is generally dependant upon the mole of atomic fraction of each element present. This material, regardless of the different element atomic fraction, produces only light in the red portion of the visible spectrum, i.e., about 600 to 700 nanometers (nm).

Laser diodes that produce shorter wavelengths not only produce different colors of radiation, but offer other advantages.

2

For example, laser diodes, and in particular edge emitting laser diodes, can be used with optical storage and memory devices (e.g. compact disks (CD) digital video disks (DVD), high definition (HD) DVDs, and Blue Ray DVDs). Their shorter wavelength enables the storage and memory devices to hold proportionally more information. For example, an optical storage device storing information using blue light can hold approximately 32 times the amount of information as one using red light, using the same storage space. There are also applications for shorter wavelength laser in medical systems and projection displays. This has generated interest in Group-III nitride material for use in laser diodes, and in particular gallium nitride (GaN). GaN can produce light in the blue and ultra violet (UV) frequency spectrums because of its relatively high bandgap (3.36 eV at room temperature). This interest has resulted in developments related to the structure and fabrication of Group-III nitride based laser diodes [For example see U.S. Pat. Nos. 5,592,501 and 5,838,786 to Edmond et al].

Group-III nitride laser diodes can require relatively high threshold currents and voltages to reach laser radiation because of optical and electrical inefficiencies. These elevated current and voltage levels can result in heat being generated during laser diode operation. In certain applications, laser diodes are driven by a pulsed signal that results in pulsed laser light being emitted from the laser diode. The heat generated within the laser diode typically does not present a problem during pulsed laser diode operation because the laser diode has the opportunity to cool during the lows of the signal. For other important applications, however, it can be desirable to drive the laser diode with a continuous wave (CW). CW operation is particularly applicable to operation with optical storage devices that can require a continuous light source for data storage and retrieval. Driving many current Group-III based laser diodes with a CW having the threshold current and voltage necessary for laser emission can result in heating that can damage or destroy the laser diode. Heat sinks or other cooling methods/devices can be employed to reduce operating heat within these laser diodes, but the methods/devices can increase the cost and complexity of the devices and can require additional space.

## **SUMMARY OF THE INVENTION**

The present invention is generally directed to laser diode epitaxial structure having improved operating characteristics and improved reliability, and methods for fabricating the epitaxial structures. The improved operating characteristics include operation as reduced current and voltage thresholds, which allow for efficient operation at reduced temperature.

One embodiment of a laser diode according to the present invention comprises an active region sandwiched between first and second waveguiding elements, and a compliance layer. The first waveguiding element is on the compliance layer with the compliance layer reducing strain between the first waveguiding element and other laser diode layers. The first waveguiding element has a higher index of refraction than a first waveguiding element in a similar laser diode without the compliance layer.

One embodiment of a Group-III nitride laser diode according to the present invention comprises an InGaN compliance layer on a GaN n-type contact layer and an AlGaN/GaN n-type strained super lattice (SLS) on said compliance layer. An n-type GaN separate confinement heterostructure (SCH) is on said n-type SLS and an InGaN multiple quantum well (MQW) active region is on the n-type SCH. A GaN p-type SCH on the MQW active region, an AlGaN/GaN p-type SLS

is on the p-type SCH, and a p-type GaN contact layer is on the p-type SLS. The compliance layer has an In percentage that reduces strain between the n-type contact layer and the n-type SLS compared to a laser diode without the compliance layer.

One embodiment of a method according to the present invention for fabricating a Group-III nitride laser diode comprises growing an n-type contact layer on a substrate at a temperature within a first growth temperature range. An n-type compliance layer is grown on said n-type contact layer at a temperature within a second growth temperature range that is lower than said first growth temperature. An n-type waveguiding element is grown on said compliance layer at a temperature within said first growth temperature range, said waveguiding element grown with a higher index of refraction compared to laser diodes without said compliance layer. An n-type separate confinement heterostructure (SCH) on said n-type waveguiding element, an active region is grown on said n-type SCH, a p-type SCH is grown on said active region, and a p-type waveguiding element is grown on said p-type SCH.

These and other further features and advantages of the invention will be apparent to those skilled in the art from the following detailed description, taken together with the accompanying drawings.

#### BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is sectional view of one embodiment of a laser diode according to the present invention at fabrication step where it has a contact layer on a substrate;

FIG. 2 is a sectional view of the laser diode in FIG. 1, with compliance layer and cap layer on the contact layer;

FIG. 3 is a sectional view of the laser diode in FIG. 2 with a strained-layer superlattice (SLS) on the cap layer;

FIG. 4 is a sectional view of the laser diode in FIG. 3 with a separate confinement heterostructure (SCH) layer on the SLS and an undoped layer on the SCH layer;

FIG. 5 is a sectional view of the laser diode in FIG. 4 with a multiple quantum well (MQW) active region on the undoped layer;

FIG. 6 is a sectional view of the laser diode in FIG. 5 with a blocking layer on the MQW active region;

FIG. 7 is a sectional view of the laser diode in FIG. 6 with a SCH layer on the blocking layer;

FIG. 8 is a sectional view of the laser diode in FIG. 7, with a SLS on the SCH layer;

FIG. 9 is a sectional view of the laser diode in FIG. 8, with a contact layer on the SLS;

FIG. 10 is a sectional view of one embodiment of a laser diode according to the present invention with contacts;

FIG. 11 is a sectional view of another embodiment of a laser diode according to the present invention with contacts; and

FIG. 12 is a sectional view of still another embodiment of a laser diode according to the present invention with contacts.

#### DETAILED DESCRIPTION OF THE INVENTION

The present invention provides high reliability, high output power nitride-based laser diode characterized by reduced threshold current densities and reduced threshold voltages. The present invention is particularly applicable to continuous wave operation laser diodes, although it can also be used in pulsed wave operation laser diodes. The reduced current and voltage thresholds result in lower heat build-up in the laser diode during operation, which in turn reduces that likelihood of damage or destruction of the device due to overheating.

The present invention is also directed to methods for fabricating laser diodes with these characteristics, and although the present invention is generally directed to nitride-based laser diodes it is understood that it can also be applied to laser diodes made of other material systems.

The improved threshold and current characteristics result in the laser diode operating at lower temperature without the need for external heat management elements, such as heat sinks. The improved laser diodes according to the present invention can operate at many different threshold currents and voltages, with preferred laser diodes operating with a threshold current of less than 5 kA/cm<sup>2</sup> and threshold voltage less than 5 volts (V). One embodiment of a laser diode according to the present invention has threshold current in the range of 2-4 kA/cm<sup>2</sup> and threshold voltage in the range of 4-5V, providing an output power of at least 25 mW. These lower threshold voltages and currents are a factor in lowering the laser diode's operating temperature.

The improved threshold current and voltage characteristics are realized by improving the waveguiding within the laser diode, such as by improving the guiding efficiency of the waveguiding elements. Each of the waveguiding elements can comprise waveguide cladding layers in the form of strained-layer superlattice (SLS). By increasing the index of refraction of the layers, guiding efficiency can be improved and less loss is experienced as light from the laser diode's active region is guided by the waveguiding elements. With less loss, stimulated emission can be achieved with lower threshold currents and voltages.

In one embodiment according to the present invention, the laser diode is made from the Group-III nitride material system and in particular is made from aluminum gallium nitride and gallium nitride material (AlGaIn/GaN). As used herein, the term "Group III nitride" refers to those semiconducting compounds formed between nitrogen and the elements in Group III of the periodic table, usually aluminum (Al), gallium (Ga), and/or indium (In). The term also refers to ternary and quaternary compounds, such as AlGaIn and AlInGaIn. As well understood by those in this art, the Group III elements can combine with nitrogen to form binary (e.g., GaN), ternary (e.g., AlGaIn and AlInGaIn), and quaternary (e.g., AlInGaIn) compounds. These compounds all have empirical formulas in which one mole of nitrogen is combined with a total of one mole of the Group III elements. Accordingly, formulas such as Al<sub>x</sub>Ga<sub>1-x</sub>N, where 0 ≤ x ≤ 1, are often used to describe them. In Group-III nitride laser diodes, the index of refraction of at least one of the waveguide elements is increased by arranging the laser diode so that aluminum (Al) mole fraction in the waveguiding element is increased.

In one embodiment according to the present invention, the waveguide elements can be fabricated with high Al content waveguide elements by employing a compliance layer to provide strain relief. Without this strain relief there is a danger of cracking and other forms of degradation when growing high Al content Group-III nitride (AlGaIn/GaN) waveguiding elements. Different compliance layers can be used with one embodiment according to the present invention comprising a low temperature (LT) high indium (In) containing indium gallium nitride (InGaIn) compliance layer, with an In percentage between 8 and 15 percent (%). Because of the reduced strain with other device layers as a result of the compliance layer, the waveguide cladding layers can have an Al content in the range of 15 to 20%, although other Al percentages can also be used. The higher Al content results in a larger difference in index of refraction with the active region which allows for the waveguide cladding layers to provide improved waveguiding.

Laser diodes according to the present invention can also have other improvements to allow for improved operating characteristics. Some of these include having the quantum well interface roughness reduced by adopting slower growth rate for the device n-type separate confinement heterostructure (SCH). Accordingly, the n-type SCH layer provides a smooth and uniform epitaxial layer upon which the quantum well active region can be formed. The p-contact resistance, and as result the threshold voltage, can also be reduced by employing a thicker and heavily doped p-type GaN cap layer and by reducing the doping level of the layers in the n-type SLS structure. Laser diodes according to the present invention can also comprise a high temperature (HT) growth p-type SCH layer and a low temperature (LT) growth p-SLS layer. The p-type SCH is grown at high temperature to assist Mg diffusion back into the p-AlGaN cap.

The present invention is described herein with reference to certain embodiments but it is understood that the invention can be embodied in many different forms and should not be construed as limited to the embodiments set forth herein. It is also understood that when an element or component is referred to as being "on", "connected to" or "coupled to" another layer, element or component, it can be directly on, connected to or coupled to the other layer element or component, or intervening elements may also be present. Furthermore, relative terms such as "inner", "outer", "upper", "above", "lower", "beneath", and "below", and similar terms, may be used herein to describe a relationship of one component or element to another. It is understood that these terms are intended to encompass different orientations of the device in addition to the orientation depicted in the figures.

Although the terms first, second, etc. may be used herein to describe various layers, elements, components and/or sections, these layers, elements, components, and/or sections should not be limited by these terms. These terms are only used to distinguish one layer, element, component, or section from another. Thus, a first layer, element, component, or section discussed below could be termed a second element, component, or section without departing from the teachings of the present invention.

Embodiments of the invention are described herein with reference to cross-sectional view illustrations that are schematic illustrations of idealized embodiments of the invention. It is understood that many of the layers will have different relative thicknesses compared to those shown and that the laser diodes will have different shapes. Further, variations from the shapes of the illustrations as a result, for example, of manufacturing techniques and/or tolerances are expected. Embodiments of the invention should not be construed as limited to the particular shapes of the regions illustrated herein but are to include deviations in shapes that result, for example, from manufacturing. A region illustrated or described as square or rectangular will typically have rounded or curved features due to normal manufacturing tolerances. Thus, the regions illustrated in the figures are schematic in nature and their shapes are not intended to illustrate the precise shape of a region of a device and are not intended to limit the scope of the invention.

Referring now to the drawings and in particular FIGS. 1-9, a laser diode 10 according to the present invention is shown at different steps in the fabrication process. A single laser diode 10 is shown, but it is understood that more typically many laser diodes are fabricated on a single substrate wafer, with the devices then being separated into individual devices using known processes, such as scribe and break processes.

Laser diodes can be formed on a substrate wafer using known fabrication processes such as growth in a reactor by

metalorganic chemical vapor deposition (MOCVD). Under some circumstances carbon can form in the semiconductor material comprising the laser diode that can interfere with light output. To minimize carbon formation, the laser diode structure can be grown at high pressure within the MOCVD reactor, such as at atmospheric pressure. Carbon build-up can also be minimized by using a high V/III ammonia ratio during growth, and by using a slower growth rate. Many different precursors can be used during MOCVD growth including but not limited to trimethylgallium (TMGa), triethylgallium (TEGa), trimethylaluminum (TMAI), triethylindium (TMIn), Bis(cyclopentadienyl)magnesium ( $\text{Cp}_2\text{Mg}$ ), silane ( $\text{SiH}_4$ ) and ammonia ( $\text{NH}_3$ ).

FIG. 1 shows one embodiment the laser diode 10 at an early step in the fabrication process comprising a substrate 12 that can be made of many different materials including but not limited to sapphire, silicon carbide, with the preferred laser diode 10 being formed on a free-standing GaN substrate or a lateral epitaxial overgrown (LEO) GaN template. N-type contact layer 14 is grown on the substrate 12 that comprises a material suitable for spreading current from an n-contact to the active region. For laser diodes that are formed on conductive substrates, the n-contact can be formed on the substrate 12 and current conducts through the substrate to the active region of the laser diode 10. For laser diodes formed on non-conductive substrates or substrates that do not efficiently spread current, a lateral geometry can be used for contacting the device. As further described below for lateral geometry, the laser diode 10 can be etched to form a mesa in the contact layer 14 and the n-contact is deposited on the contact layer mesa. Current spreads from the contact, through the n-type layer 14 and to the laser diode's active region.

It is also understood that laser diodes formed on a conductive substrate can effectively spread current without the n-type contact layer 14, and that these embodiments can be arranged without the contact layer 14. It is further understood that other embodiments of the present invention can have the substrate removed, and in those embodiments contact can be made directly to the epitaxial layers.

The n-type contact layer 14 can be made of many different elements/materials doped with different elements in different densities. The preferred contact layer 14 comprises GaN doped with silicon (Si) having a doping density being between  $1\text{E}17$  to  $1\text{E}19\text{ cm}^{-3}$ . The contact layer 14 is normally grown at high temperature (e.g. 1000 to 1100° C.) and the preferred growth rate is 1.5 to 3  $\mu\text{m/hr}$ . The preferred MOCVD growth carrier gas is hydrogen with a 50%  $\text{H}_2$ /50%  $\text{N}_2$  subflow.

FIG. 2 shows the laser diode 10 after additional growth steps to form a compliance layer 16 on the contact layer 14. The compliance layer is included to allow waveguiding elements to be grown with higher index of refraction, which in turn allows for the threshold current of laser operation to be lower. As described below, the waveguiding elements of some embodiments of the laser diode according to the present invention comprise waveguiding epitaxial layers that can be arranged in many different ways and can comprise many different structures. In one embodiment according to the present invention, the waveguiding epitaxial layers comprise a strained layer superlattice (SLS) made of AlGaN/GaN. The higher the Al content of the SLS the higher the index of refraction and the more efficient the guiding of active region light. Without the compliance layer, however, a good quality SLS may not be reliably formed. The strain between the contact layer 14 and the SLS structure could cause the high Al content layers to degrade or crack.

To reduce the danger of degradation and cracking, the compliance layer **16** includes one or more elements that help reduce the strain between the contact layer **14** and SLS. In the one embodiment according to the present invention, the compliance layer **16** can comprise n-type  $\text{In}_x\text{Ga}_{1-x}\text{N}$  layer grown by with Si doping. The In element in the compliance layer provides for the strain relief, with the desirable In composition (x) being between 0.08 and 0.12. It is understood that other compositions of (x) are also acceptable such as 0 to 0.08 and 0.12 to 0.20 or more. Many different Si doping densities can also be used with a suitable doping density being between  $1\text{E}17$  to  $1\text{E}19\text{ cm}^{-3}$ . The preferred MOCVD growth carrier gas is nitrogen which assists in higher In incorporation, and the subflow can be 100%  $\text{N}_2$ .

Because of the In element in the compliance layer, however, the compliance layer is typically grown at temperatures lower than the growth temperature of typical AlGaIn/GaN layers. This lower temperature growth encourages In incorporation into the material. Typical growth temperatures for InGaIn are in the range of  $700$  to  $1000^\circ\text{C}$ . A, with a suitable growth temperature being  $900^\circ\text{C}$ . Subsequent device layers of AlGaIn/GaN can be grown at temperatures in the range of  $1050$ - $1100^\circ\text{C}$ . These elevated temperatures present a danger of desorption or burning of the In within the compliance layer **16**, that can negatively impact the operation and efficiency of the laser diode **10**. To help reduce the danger, a thin low-temperature (LT) n-type GaN:Si first cap layer **18** can be grown on the compliance layer to cap and protect the InGaIn compliance layer **16**. Growth of GaN at  $900^\circ\text{C}$ . is relatively slow but can be used because the cap layer is relatively thin. Growth at this temperature also provides the advantage of not significantly damaging or degrading the In in the InGaIn compliance layer. The cap layer **18** protects the InGaIn compliance layer **16** during the temperature ramp-up for faster growth of subsequent layers.

FIG. **3** shows the laser diode **10** after additional growth steps, with an n-type SLS **20** formed on the cap layer **18** and compliance layer **16**, with the cap layer **18** between the compliance layer **16** and the n-type SLS **20**. The n-type SLS **20** can comprise different layers made of many different materials, with a preferred SLS being an n-type  $\text{Al}_x\text{Ga}_{1-x}\text{N}$ /GaN:Si modulation-doped SLS. The SLS is preferably grown by Si-doping the GaN layer(s) only. The preferred thickness of the AlGaIn and GaN:Si layers is between  $2$ - $3\text{ nm}$  and the desirable growth rate is between  $0.5$ - $2\text{ A/s}$ , which encourages Al incorporation at high pressure during growth of the AlGaIn layers. The preferred growth carrier gas is hydrogen with  $50\%$   $\text{H}_2$ / $50\%$   $\text{N}_2$  subflow and high growth temperature is normally desired (e.g. approximately  $1050^\circ\text{C}$ .). The doping density of the GaN layer(s) is between  $1\text{E}17$  to  $1\text{E}19\text{ cm}^{-3}$  and the most desirable

As discussed above, the compliance layer **16** allows for reliably growth of the n-type SLS **20** with a higher Al composition than could be grown without the presence of the compliance layer. The higher Al content allows the n-type SLS **20** to more efficiently reflect light emitted by the laser diode's active region. The  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  layer(s) of the n-type SLS **20** preferably have an (x) composition between  $0.15$  and  $0.2$ . Composition (x) in the ranges of  $0.1$  to  $0.15$  and  $0.2$  to  $0.3$ , as well as other compositions are also acceptable. Higher Al compositions, however, can result in lower conductivity due to the increase in the ionization energy of the Si dopant. Lower Al compositions can result in poor wave-guiding because of reduced refractive-index of the SLS **20**. The SLS **20** can have many different thicknesses, with a preferred thickness being between  $0.6$  to  $1.5\text{ }\mu\text{m}$ .

FIG. **4** shows the laser diode **10** with an n-type separate confinement heterostructure (SCH) layer **22** formed on the SLS **20**. The SCH layer **22** serves as part of the light path to the edges of the laser diode **10** and ultimately out the emission edge of the laser diode **10**. The light from the active region traveling toward the waveguiding elements (n-type SLS **20** and the p-type SLS described below) is reflected, and light traveling toward the laser diode's edges is reflected until stimulated emission is out one of the edges. The n-type SCH layer **22** and p-type SCH layer serve as the primary reflection cavity for this reflected light.

SCH **22** can comprise many different materials doped in different densities by different elements. A preferred n-type SCH comprises an n-type GaN grown with Si doping at a doping density between  $1\text{E}17$  to  $1\text{E}18\text{ cm}^{-3}$ . The SCH can have many different thicknesses, with the preferred thickness being in the range of  $0.07$  to  $0.15\text{ }\mu\text{m}$ . The preferred growth rate is in the range of  $0.5$  to  $2\text{ A/s}$  to make the top surface of the SCH smooth and the preferred growth carrier gas is nitrogen with  $100\%$   $\text{N}_2$  subflow. By keeping the SCH **22** top surface smooth, subsequent layers can be grown with better quality. For example, the active region can be grown with layers having more uniform thickness such that the active region can emit light with a more uniform wavelength.

A thin undoped GaN layer **24** can be included on the n-type SCH, before growth of the multiple quantum well (MQW) active region. By having an undoped intrinsic material adjacent to the MQW active region, dopants are inhibited from flowing into the active region absent a driving current. The preferred thickness of the undoped GaN layer **24** is between  $5$ - $12\text{ nm}$ . The desired growth rate is between  $0.3$  to  $1.0\text{ A/s}$  to make the layers smooth and the preferred growth carrier gas is nitrogen with a  $100\%$   $\text{N}_2$  subflow.

FIG. **5** shows the laser diode **10** with an active region **26** formed on the undoped GaN layer **24**. The active region can comprise different layers arranged in different ways, with a preferred active region comprising a MQW region that can have different numbers of quantum wells and barrier layers. The preferred MQW region having three quantum wells. Quantum wells are included for confinement of electrons and holes to encourage recombination and the resulting light emission. In general, the larger the number of quantum wells within the MQW region typically results in increased gain volume. The greater the number of quantum wells in the MQW region also typically results in a higher necessary threshold voltage. Three quantum wells allows for a good combination of current density gain with a relatively low threshold voltage.

In one embodiment according to the present invention, MQW active region **26** comprises three quantum wells and associated barrier layers in an  $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{In}_y\text{Ga}_{1-y}\text{N}$  stack. The desirable composition of the quantum wells had (x) between  $0.8$  to  $0.12$  and that of the barrier layer has (y) between  $0$  to  $0.04$  for an approximate  $405\text{ nm}$  emission wavelength. The desired well width is between  $3$ - $5\text{ nm}$  and the desired barrier width is between  $4$ - $8\text{ nm}$ . The preferred growth temperature is relatively low, between  $800$  to  $950^\circ\text{C}$ . to assist in In incorporation and is grown in nitrogen carrier gas with  $100\%$   $\text{N}_2$  subflow. The desired growth rate is slow, between  $0.3$  to  $0.6\text{ A/s}$ , to make the interfaces smooth and to lower carbon incorporation into the active region. The preferred way of terminating the MQW region is by having a last well instead of a barrier.

FIG. **6** shows the laser diode **10** with an electron blocking layer **28** formed on the MQW active region **26**. The blocking layer **28** comprises a material that blocks electrons from passing from the MQW active region **26** into the p-type SCH

layer (shown in FIG. 7 and described below), but lets holes pass through to from the p-type SCH layer to the MQW active region 26. By blocking electrons, the blocking layer encourages recombination in the MQW active region 26.

The blocking layer 26 can be made of many different materials doped in different ways. A suitable material p-type  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  achieved by Mg doping and a suitable thickness of the layer is between 15-25 nm. The preferable method of depositing the layer is by a two step deposition process. First, a 1-10 nm AlGaIn layer is grown at lower temperature, preferably between 800 to 950° C. This low temperature growth helps reduce desorption and damage to the In in the MQW active region 26 that can be caused by higher temperatures. Second, the remaining blocking layer is grown at an elevated temperature, preferably between 900 to 1050° C. The preferred Al composition (x) of the blocking is between 0.15 to 0.25 and the desirable Mg doping concentration is between  $7\text{E}18$  and  $3\text{E}19^{-3}$ . The preferred growth carrier gas during deposition of the blocking layer 28 is nitrogen with a 100%  $\text{N}_2$  subflow and the preferred growth rate is 1-2 Å/s.

FIG. 7 shows the laser diode 10 having p-type separate confinement heterostructure (SCH) layer 30 formed on the blocking layer 28. The p-type SCH 30 can be made of many different materials doped in many different ways, with a preferred p-type SCH 30 made of p-type GaN grown with Mg-doping. As described above, the p-type SCH layer 30, along with the n-type SCH layer 22, serves as the primary light path out of the laser diode 10 between the waveguiding elements. The preferred Mg doping density of the p-type SCH layer is between  $1\text{E}18$  to  $5\text{E}19\text{ cm}^{-3}$  and the preferred thickness range is between 0.07-0.15  $\mu\text{m}$ . The preferred growth rate is between 1-2 Å/s to make the layers smooth and the preferred carrier gas is hydrogen with a 50%  $\text{H}_2$ /50%  $\text{N}_2$  subflow. The growth temperature for this layer is relatively high such as between 1000-1100° C. to assist uniform Mg diffusion in the p-AlGaIn cap layer.

FIG. 8 shows the laser diode 10 with a p-type SLS 32 grown on the p-type SCH layer 30. The p-type SLS 32 can be made of many different layers and materials arranged in different ways but is preferably p-type  $\text{Al}_x\text{Ga}_{1-x}\text{N}$ /GaIn:Mg modulation-doped SLS grown Mg acceptors (dopants) in the GaN layer only. The preferred thickness of the AlGaIn and the GaIn:Mg layer is between 2-3 nm and the preferred growth rate is between 0.5-1 Å/s to assist Al incorporation at high pressure. The preferred growth carrier gas is hydrogen with a 50%  $\text{H}_2$ /50%  $\text{N}_2$  subflow. Lower growth temperature between 850-950° C., can be utilized to reduce In segregation in the underlying active region 26 during the long p-type SLS growth step at high temperature. The desired acceptor density is between  $8\text{E}18$  to  $5\text{E}19\text{ cm}^{-3}$  the desirable Al composition (x) is between 0.15 and 0.2. Compositions (x) in the range 0.1-0.15 and 0.2 and 0.3 are also acceptable. Higher Al composition results in lower conductivity due to the increase in the ionization energy of the Mg dopant. Lower Al composition results in poor wave-guiding because of reduced difference in refractive-index between the active layer and the cladding layer. The preferred p-type SLS 32 thickness is between 0.6-1.5  $\mu\text{m}$ . Thinner SLS can result in poor waveguiding and thicker SLS can result in cracking due to strain.

FIG. 9 shows the laser diode 10 capped with a thin p-type contact layer 32 that can be made of different materials doped in different ways, but is preferably p-type GaN by means of Mg-doping. The preferred doping density should be relatively high, with one embodiment having a doping density between  $1\text{E}19$  to  $5\text{E}20\text{ cm}^{-3}$ . A doping ramp from low to high concentration can be utilized instead of a uniform doping

concentration. In some embodiments a uniformly doped contact layer 32 that is heavily doped can be hazy, which can interfere with efficient operation. By ramping up the doping concentration such that the last portion of the contact layer 32 is highly doped, the contact layer typically will not turn haze. The preferred thickness range for the contact layer is between 20-50 nm and a suitable growth rate is between 0.5-2 Å/s. The preferred carrier gas is hydrogen with a 50%  $\text{H}_2$ /50%  $\text{N}_2$  subflow and the growth preferably is at relatively high temperature between 1000-1100° C.

The p-GaN cap layer 34 has relatively high doping and optimum thickness to allow for reduced threshold voltage. The higher the doping and the thinner the cap layer, the lower the Schottky barrier at the contact layer junction because of electron tunneling. The contact layer 34, however, cannot be too thin because the layer can then experience non-uniform doping. The contact layer 34 should have a sufficient thickness to allow for uniform layer doping. The p-type SLS structure 32 has lower doping (but high Al content) compared to the p-type cap layer 34, to reduce threshold voltage. With higher doping of the SLS structure, there is a danger that precipitants from the doping material (e.g. Mg) can form that can be resistive. This can result in higher operating threshold voltage. The lower doping, such as in the range described above, can provide good quality materials with no precipitates. This combination of highly doped and optimum thickness p-type cap layer 34 with lower doped p-type SLS structure 32, can provide reduced threshold voltage for laser diode 10.

FIG. 10 shows an embodiment of a laser diode 50 having features described above to provide for low threshold current and voltage operation. For ease of illustration the specific layers are not shown in detail, but it is understood that the layers can be arranged as those shown in FIGS. 1-9. The laser diode 50 further comprises a p-contact 52 on the top surface of the laser diode 30, which will typically be the p-type contact layer 34 shown in FIG. 9 and described above. The p-contact can comprise many different materials, but is preferably formed of combinations of nickel, gold and platinum (Ni/Au/Pt) deposited using known methods such as sputtering. The laser diode 50 further comprises an n-contact 54 on the substrate 12 that is shown in the FIGS. 1-9 and described above. For laser diode 50 the substrate is conductive, which allows re-contact to be formed directly on the substrate. The re-contact can also be made of many different materials with suitable materials being combinations of titanium and aluminum (Ti/Al). Current from the n-contact 54 flow through the substrate to the laser diode's active region. Pad metals can then be included on one or both of the p- and n-contacts 52, 54 and one or both can include an electrical connection, such as through a wire bond. In other embodiments, the n-contact can be directly connected to a submount such as a printed circuit board (PCB).

It is understood that the laser diode 50 can also operate without a substrate, with the substrate being removed following growth of the laser diode. In those embodiments without the substrate the n-contact can be on other layers such as the n-type contact layer shown as 14 in FIGS. 2-9 and described above, or on other layers.

FIG. 11 shows still another embodiment of a laser diode 60 according to the present invention with a p-contact 62 and n-contact 64. The upper portion of the laser diode 60 has been etched to form a ridge through the upper portion of the laser diode 60. The ridge is arranged to provide optical and electrical confinement during operation to increase efficiency. The p-contact is again on the top surface of the laser diode 60, which is also the top surface of the ridge 66 and is also the

## 11

p-type contact layer 34 (FIG. 9). The laser diode 60 also has a conductive substrate that allows for the n-type contact to be formed on the substrate. The p- and n-type contacts 62, 64 can be made of the same material as contacts 52, 54 shown in FIG. 10 and described above, and pad metals can also be included on one or both of the contacts 62, 64. In other embodiments the n-contact can be contacted through a submount or PDB that the laser diode 60 is mounted to.

FIG. 12 shows a laser diode 70 also comprising a p-contact 72, n-contact 74 and a ridge 76, with the p-contact on the top surface of the ridge 76. For laser diode 70, however, the substrate is not conductive, and as a result the n-contact 74 cannot be formed on the substrate. Instead, a portion of the laser diode 70 is removed down to the n-type contact layer (element 14 described above and shown in FIGS. 2-9), such as by etching. A mesa 78 is formed in the n-contact layer for the n-contact 74. Current flows from the n-contact 74 through the n-contact layer and to the active region of the laser diode 70. The p- and n-type contacts can be made of the same material as those described above and can be deposited using the same methods. Pad metals can be included on one or both of the contacts 72, 74 and electrical connection can be made to both, such as through wire bonds.

Although the present invention has been described in considerable detail with reference to certain preferred configurations thereof, other versions are possible. Therefore, the spirit and scope of the appended claims should not be limited to their preferred versions contained therein.

We claim:

1. A method for fabricating a Group-III nitride laser diode, comprising:

- growing an n-type contact layer on a substrate at a temperature within a first growth temperature range;
- growing an n-type compliance layer on said n-type contact layer at a temperature within a second growth temperature range that is lower than said first growth temperature;
- growing a cap layer on said compliance layer at a temperature in said second temperature range to protect said compliance layer from temperatures in said first temperature range used to grow subsequent layers;
- growing an n-type waveguiding element and on said cap layer at a temperature within said first growth temperature range, said waveguiding element grown with a higher index of refraction compared to laser diodes without said compliance layer;
- growing an n-type separate confinement heterostructure (SCH) on said n-type waveguiding element;
- growing an active region on said n-type SCH;
- growing an undoped layer adjacent said active region on said n-type SCH;
- growing a p-type SCH on said active region; and
- growing a p-type waveguiding element on said p-type SCH.

2. The method of claim 1, wherein said active region comprises multiple quantum wells.

3. The method of claim 2, wherein said active region comprises three quantum wells.

4. The method of claim 1, further comprising growing a p-type contact layer on said p-type SLS at a temperature within said first temperature range.

5. A method for fabricating a Group-III nitride laser diode, comprising:

- growing an n-type contact layer on a substrate at a temperature within a first growth temperature range;

## 12

growing an n-type compliance layer on said n-type contact layer at a temperature within a second growth temperature range that is lower than said first growth temperature;

growing a cap layer on said compliance layer at a temperature in said second temperature range to protect said compliance layer from temperatures in said first temperature range used to grow subsequent layers;

growing an n-type waveguiding element and on said cap layer at a temperature within said first growth temperature range, said waveguiding element grown with a higher index of refraction compared to laser diodes without said compliance layer;

growing an n-type separate confinement heterostructure (SCH) on said n-type waveguiding element;

growing an active region on said n-type SCH;

growing a p-type SCH on said active region; and

growing a p-type waveguiding element on said p-type SCH, wherein said n-type SCH, active region and p-type waveguiding element are grown at a temperature within said second growth temperature range, and said p-type SCH is grown at a temperature within said first temperature range.

6. The method of claim 1, wherein said first temperature range is from 1000 to 1100° C.

7. The method of claim 1, wherein said second temperature range is from 700 to 1000° C.

8. The method of claim 1, wherein said n-type contact layer comprises GaN grown at a rate in the range of 1.5 to 3 μm/hr and with a silicon doping density in the range of 1E17 to 1E19 cm<sup>-3</sup>.

9. The method of claim 1, wherein said compliance layer comprises In<sub>x</sub>Ga<sub>1-x</sub>N wherein x is in the range of 0 to 0.20 and the Si doping density is in the range of 1E17 to 1E19 cm<sup>-3</sup>.

10. The method of claim 1, wherein said n-type waveguiding element comprises an n-type Al<sub>x</sub>Ga<sub>1-x</sub>N/GaN strained layer superlattice (SLS).

11. The method of claim 10, wherein said n-type Al<sub>x</sub>Ga<sub>1-x</sub>N/GaN SLS has x in the range of 0.1 to 0.3 and wherein said GaN layers have a Si doping density in the range of 1E17 to 1E19 cm<sup>-3</sup>.

12. The method of claim 1, wherein said n-type SCH comprises GaN grown at a rate in the range of 0.5 to 2 A/s with a Si doping density in the range of 1E17 to 1E18 cm<sup>-3</sup>.

13. The method of claim 1, wherein said n-type SCH has a thickness in the range of 0.07 to 0.15 μm.

14. The method of claim 1, wherein said active region comprises an In<sub>x</sub>Ga<sub>1-x</sub>N/In<sub>y</sub>Ga<sub>1-y</sub>N multiple quantum well stack with x in the range of 0.8 to 0.12, and y in the range of 0 to 0.04, and a growth rate in the range of 0.3 to 0.6 A/s.

15. The method of claim 1, wherein said active region comprises three quantum wells with surrounding barrier layers, the width of each said quantum well in the range of 3-5 nm, and each barrier layer width in the range of 4-8 nm.

16. The method of claim 1, wherein said p-type SCH comprises GaN grown at a rate in the range of 1-2 A/s with a Mg doping density of 1E18 to 5E19 cm<sup>-3</sup> and a thickness in the range of 0.07 to 0.15 μm.

17. The method of claim 1, wherein said p-type waveguiding element comprises a p-type Al<sub>x</sub>Ga<sub>1-x</sub>N/GaN strained layer superlattice (SLS) with x in the range of 0.1 to 0.3 and said GaN is Mg doped at a density in the range of 8E18 to 5E19 cm<sup>-3</sup>.

18. The method of claim 17, wherein the growth rate of said p-type SLS is in the range of 0.5 to 1 A/s.

19. The method of claim 4, wherein said p-type contact layer comprises p-type GaN doped with a Mg doping density

## 13

in the range of  $1\text{E}19$  to  $5\text{E}20\text{ cm}^{-3}$ , grown at a rate in the range of  $0.5$  to  $2\text{ A/s}$  to a thickness in the range of  $20$  to  $50\text{ nm}$ .

20. The method of claim 4, wherein said p-type contact layer is grown with a ramp-up in doping density.

21. The method of claim 4, wherein said p-type contact layer is grown with a ramp-up in doping density. 5

22. The method of claim 1, further comprising growing a p-type electron blocking layer on said active region at prior to growing said p-type SCH.

23. The method of claim 22, wherein said blocking layer comprises p-type  $\text{Al}_x\text{Ga}_{1-x}\text{N}$ , where  $x$  is in the range of  $0.15$  to  $0.25$ , having an Mg doping in the range of  $7\text{E}18$  to  $3\text{E}19\text{ cm}^{-3}$  and a thickness in the range of  $15$ - $25\text{ nm}$ . 10

24. A method for fabricating a Group-III nitride laser diode, comprising: 15

growing an n-type contact layer on a substrate at a temperature within a first growth temperature range;

growing an n-type compliance layer on said n-type contact layer at a temperature within a second growth temperature range that is lower than said first growth temperature; 20

## 14

growing a cap layer on said compliance layer at a temperature in said second temperature range to protect said compliance layer from temperatures in said first temperature range used to grow subsequent layers;

growing an n-type waveguiding element and on said cap layer at a temperature within said first growth temperature range, said waveguiding element grown with a higher index of refraction compared to laser diodes without said compliance layer;

growing an n-type separate confinement heterostructure (SCH) on said n-type waveguiding element;

growing an active region on said n-type SCH;

growing a p-type SCH on said active region;

growing a p-type waveguiding element on said p-type SCH; and

growing a p-type electron blocking layer on said active region at prior to growing said p-type SCH, wherein the first  $1$ - $10\text{ nm}$  of said blocking layer is grown at a temperature within said second growth temperature range, and the remaining of said blocking layer is grown at a temperature within said first growth temperature range.

\* \* \* \* \*